

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a ceramic film, comprising:  
providing a treatment target in which a raw material body including a complex oxide and a metal material including lead or bismuth included in the complex oxide in an amount of at most 5% in excess of a stoichiometric composition is applied to a substrate,  
holding the treatment target in a chamber,  
supplying a gas which includes at least an oxidizing gas to the chamber, the oxidizing gas being heated to a first temperature in advance; and  
crystallizing the raw material body by increasing pressure of the gas in the chamber to a predetermined pressure of ~~two~~ 9.9 atmospheres ~~or more~~ and heating the treatment target to a second temperature in the chamber by a heat treatment to obtain a ferroelectric ceramic,  
wherein a capacity of the chamber is 100 times or less of a volume of the substrate,  
wherein the treatment target is heated by a heating mechanism provided outside of the ~~chamber; and~~ chamber,  
wherein the heat treatment is performed by using a rapid thermal annealing ~~method; method, and~~  
wherein the treatment target is heated to the second temperature at a temperature rise rate of 50°C/sec or more.
- 2-4. (Canceled)

5. (Original) The method of manufacturing a ceramic film as defined in claim 1, wherein pressure of the gas in the chamber is increased to the predetermined pressure of two atmospheres or more within 60 seconds.

6. (Previously Presented) The method of manufacturing a ceramic film as defined in claim 1, wherein the gas is supplied to the chamber after being heated in advance to the first temperature of 200°C or less.

7-8. (Canceled)

9. (Previously Presented) The method of manufacturing a ceramic film as defined in claim 1, wherein the capacity of the chamber is 10 times to 50 times of a volume of the treatment target.